TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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POWER GaAs MMIC

TMD0708-2

Features:

■ HIGH POWER

P1dB= 33 dBm at 7.1 to 8.5 GHz

HIGH GAIN

GldB= 22 dB at 7.1 to 8.5 GHz

■ BROAD BAND INTERNALLY MATCHED

■ HERMETICALLY SEALED PACKAGE

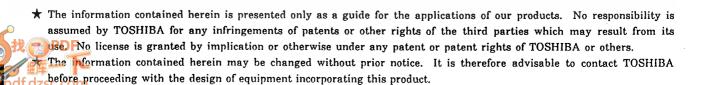
ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

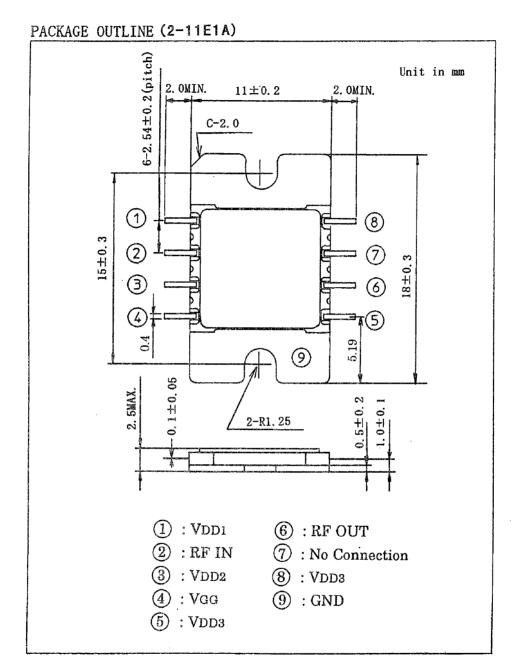
CHARACTERISTICS	SYMBOL	UNIT	RATINGS
DRAIN SUPPLY VOLTAGE	VDD	V	15
GATE SUPPLY VOLTAGE	VGG	V	-10
INPUT POWER	Pin	W	0. 1
FLANGE TEMPERATURE	Tf	$^{\circ}$	-30~+80
STORAGE TEMPERATURE	Tstg	$^{\circ}$	$-65\sim+175$

RF CHARACTERISTICS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1 dB	P1dB	VDD1=VDD2=VDD3=	dBm	32.0	33. 0	-
Gain Compression Point	-17	10V,				
Power Gain at 1 dB	G1dB	VGG=-5 V	dB	20.0	22. 0	_
Gain Compression Point	DIS	f= 7.1-8.5 GHz				
Drain Current	IDD *		A		1.70	2.00
Input VSWR	VSWRi		_		_	3.0

^{*} IDD=IDD1+IDD2+IDD3





HANDLING PRECAUTIONS FOR PACKAGED TYPE

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260%. Flanges of devices should be attached using screws and washers. Recommended torques are $0.18\text{-}0.20~\text{N}\cdot\text{m}$.